



# BN10(2CN3,BZU1)

## GLASS PASSIVATED SILICON DAMPING DIODE

### Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: QZJ840611



### TECHNICAL DATA:

( $T_a = 25^\circ\text{C}$ )

Parameter name	Symbols	Unit	Specifications	Test Condition
Use for			Rectifier, damping circuit.	
Store temperature	T	$^\circ\text{C}$	-55~+150	
Quality Class			GS	
Peak Repetitive Reverse Voltage	$V_{RRM}$	V	50~1400	
Average Forward Current	$I_{F(AV)}$	A	1.0	
Peak Forward Voltage	$V_{FM}$	V	A~G: 1.8 H~J: 2.5	$I = A I_{F(AV)}, A = 3.1415926$
Average Forward Voltage	$V_F$	V	1.0	$I = I_{F(AV)}$
Non-repeat Forward Surge Current	$I_{FSM}$	A	30	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	$I_{RM1}$	$\mu\text{A}$	10	$V_R = V_{RRM}, T_a = 25^\circ\text{C}$
Peak Reverse Current	$I_{RM2}$	$\mu\text{A}$	200	$V_R = V_{RRM}, T_a = 125^\circ\text{C}$
Junction Temperature	$T_{jm}$	$^\circ\text{C}$	150	
Reverse Recovery Time	$t_{rr}$	$\mu\text{S}$	4	$V_R = 10\text{V}, I_F = 50\text{mA}, R_L = 75\text{ohms}$

### SPECIFICATIONS:

A	B	C	D	E	F	G	H	I	J
50V	100V	200V	300V	400V	600V	800V	1000V	1200V	1400V

Outline and Dimensions: